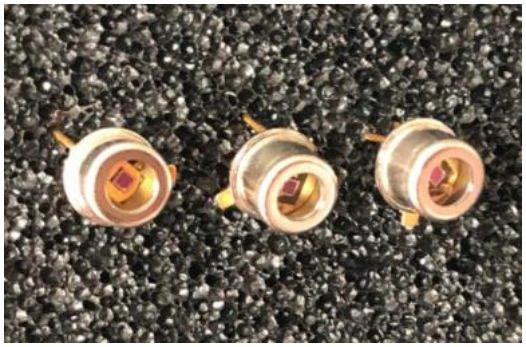
High speed Photodiode

OSX0838



Description

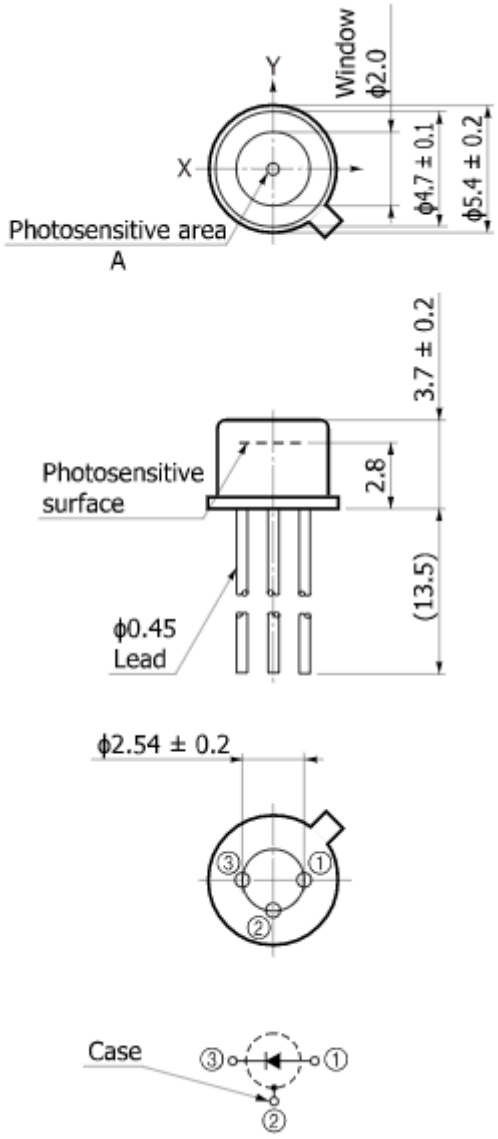
The OSX0838 is high speed, high sensitivity silicon Photodiode with high bandwidth.

Features

* High speed response
* Low dark current
* High reliability in demanding environments
* Operating temperature is from -40 to +80℃
*Storage temperature is from -40 to +100℃

Applications

* High speed photometry
* High speed switch
* pulse light detection
* High speed optical communications
* Fiber optic light monitoring



NOTES:

All dimension are in millimeters.

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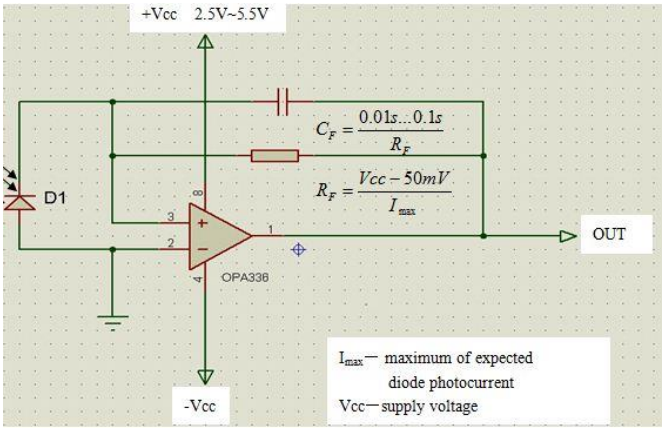
Absolute Maximum Ratings (Ta=25℃)

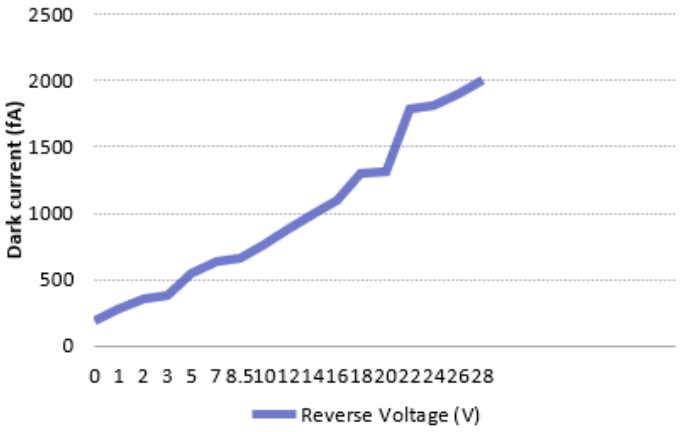
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	S			1.016*1.。016		mm
Active area	A			0.838*0.838		mm
Dark current	I_D	VR=0V		0.20		nA
Temp coefficient of I_D	T_{CID}			0.18		times/℃
Rise time	t_R	V_R=5V;λ=850nm;R_L=50Ω		1		ns
Reverse breakdown voltage	$V_{(BR)R}$	I_R=30μA Ev=0lx	70	150		V
Junction Capacitance	C_J	V_R=3V f=1MHz		5.6		pF
Photo sensitivity	S_R	830nm		0.54		A/W
Spectral Application Range	λ_{range}		400		1100	nm
Spectral Response-Peak	λ_p			830		
Shunt resistance	R_{sh}	V_R=10mV		50		MΩ
Rsh Temperature Coefficient	TC R_{sh}	Ev=100lx , VR=10mV		0.18		%/℃
Angular Resp 50% Resp Pt	$\theta_{1/2}$			±35		Degrees
Noise Equivalent Power	NEP	V_R =0V λ=830nm		1.6×10^{-14}		$W/Hz^{1/2}$
Specific Detectivity	D*	V_R =0V λ=830nm		4.3×10^{13}		$cm(Hz/W)^{1/2}$

Application Circuit:

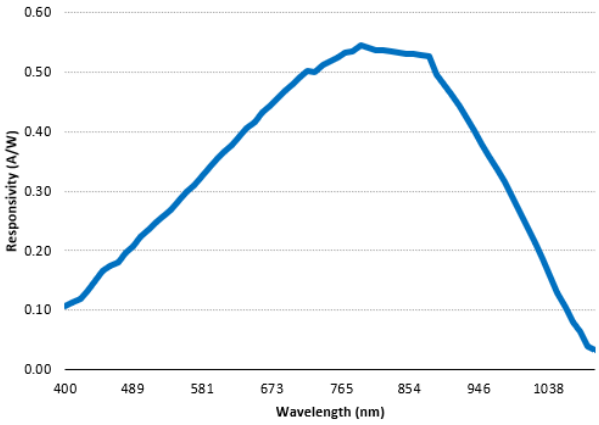


Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject change without notice

■Dark current vs. reverse voltage



■ Spectral response



■ Capacitor vs. reverse voltage